

AMENDMENTS TO THE CLAIMS

The following listing of claims will replace all prior versions and listings of claims in the application.

LISTING OF CLAIMS

1. (Currently Amended) A semiconductor device comprising:
 - a gate insulating film that includes nitrogen (N^+) ions and that is provided on a semiconductor layer;
 - a gate electrode provided on the gate insulating film; ~~and~~
 - a source region and a drain region provided in the semiconductor layer at two sides of the gate electrode;
 - wherein the source and the drain regions comprise:
 - first impurity diffusion layers formed of a specific impurity introduced in the semiconductor layer adjacent two sides of the gate electrode; and
 - second impurity diffusion layers provided in the semiconductor layer adjacent the first impurity diffusion layers and opposite from the gate electrode, the second impurity diffusion layers being in contact with the first impurity diffusion layers;
 - and
 - a nitrogen diffusion layer formed under the gate insulating film from the N^+ ions in the gate insulating film,
 - wherein the first impurity diffusion layers comprise:
 - a diffusion suppression impurity for suppressing diffusion of the specific impurity into the semiconductor layer.

2. (Original) The semiconductor device according to Claim 1, wherein the diffusion suppression impurity is located in the semiconductor layer under the gate electrode.

3-5. (Cancelled)

6. (Currently Amended) A semiconductor device comprising:
a gate insulating film that includes nitrogen (N^+) ions and that is provided
on a semiconductor layer;
a gate electrode provided on the gate insulating film; and
a source region and a drain region provided in the semiconductor layer
along two sides of the gate electrode;
wherein the source and drain regions comprise:
first impurity diffusion layers adjacent the two sides of the gate electrode,
the first impurity diffusion layers including a specific impurity; and
second impurity diffusion layers abutting the first impurity diffusion layers
opposite the gate electrode; and
a nitrogen diffusion layer formed under the gate insulating film from the N^+
ions in the gate insulating film,
wherein the specific impurity diffusion layers comprise:
a diffusion suppression impurity that suppresses diffusion of the specific
impurity into the semiconductor layer.